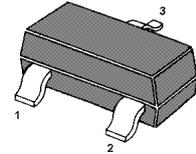
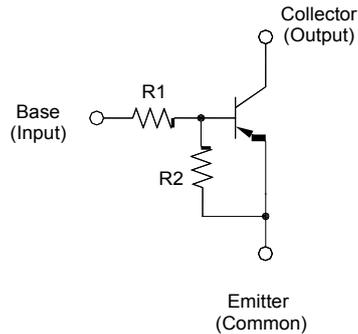


PNP Silicon Epitaxial Planar Transistor

for high current switching, interface circuit and driver circuit application.

Feature

- With built-in bias resistor
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Resistor Values

Type	R1 (KΩ)	R2 (KΩ)
MMBTRA221SS	1	1
MMBTRA222SS	2.2	2.2
MMBTRA223SS	4.7	4.7
MMBTRA224SS	10	10
MMBTRA225SS	1	10
MMBTRA226SS	2.2	10

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Output Voltage	$-V_o$	50	V
Input Voltage	$-V_i$	10, -10	V
		12, -10	
		20, -10	
		30, -10	
		10, -5	
		12, -6	
Output Current	$-I_o$	300	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_o = 5\text{ V}$, $-I_o = 50\text{ mA}$					
MMBTRA221SS	G _I	33	-	-	-
MMBTRA222SS		39	-	-	-
MMBTRA223SS		47	-	-	-
MMBTRA224SS		56	-	-	-
MMBTRA225SS		56	-	-	-
MMBTRA226SS		56	-	-	-
Output Cutoff Current at $-V_o = 30\text{ V}$	$-I_{O(OFF)}$	-	-	10	μA
Input Current at $-V_i = 5\text{ V}$					
MMBTRA221SS	-I _I	-	-	7.2	mA
MMBTRA222SS		-	-	3.8	
MMBTRA223SS		-	-	1.8	
MMBTRA224SS		-	-	0.88	
MMBTRA225SS		-	-	7.2	
MMBTRA226SS		-	-	3.6	
Output Voltage at $-I_o = 10\text{ mA}$, $-I_i = 0.5\text{ mA}$	$-V_{O(ON)}$	-	-	0.6	V
Input Voltage (ON) at $-V_o = 0.3\text{ V}$, $-I_o = 20\text{ mA}$					
MMBTRA221SS	-V _{I(ON)}	-	-	3	V
MMBTRA222SS		-	-	3	
MMBTRA223SS		-	-	3	
MMBTRA224SS		-	-	3	
MMBTRA225SS		-	-	3	
MMBTRA226SS		-	-	2	
Input Voltage (OFF) at $-V_o = 5\text{ V}$, $-I_o = 0.1\text{ mA}$					
MMBTRA221SS~224SS	-V _{I(OFF)}	0.5	-	-	V
MMBTRA225SS~226SS		0.3	-	-	
Transition Frequency at $-V_o = 10\text{ V}$, $-I_o = 5\text{ mA}$, $f = 100\text{ MHz}$	f _T ¹⁾	-	200	-	MHz

1) Characteristic of transistor only.

